Varra Rajagopal Reddy

List of Publications by Year
in descending order

171	2,897	186209 28	276775 41
papers	citations	h-index	g-index

173	173	173	1801
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of Temperature on the Electrical and Current Transport Properties of Au/Nd2O3/n-GaN Metal/Interlayer/Semiconductor (MIS) Junction. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	1.1	6
2	Electrical and carrier transport properties of Ti/Î±-amylase/p-InP MPS junction with a Î±-amylase polymer interlayer. Journal of Materials Science: Materials in Electronics, 2021, 32, 8092-8105.	1.1	9
3	Potato Chip-Like 0D Interconnected ZnCo2O4 Nanoparticles for High-Performance Supercapacitors. Crystals, 2021, 11, 469.	1.0	16
4	Effects of Rapid Thermal Annealing on the Structural, Optical, and Electrical Properties of Au/CuPc/n-Si (MPS)-type Schottky Barrier Diodes. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	1.1	9
5	Influence of tin oxide (SnO2) interlayer on the electrical and reverse current conduction mechanism of Au/n-InP Schottky junction and its microstructural properties. Thin Solid Films, 2021, 740, 139001.	0.8	10
6	Temperature-dependent Schottky barrier parameters of Ni/Au on n-type (001) Î²-Ga2O3 Schottky barrier diode. Vacuum, 2020, 171, 109012.	1.6	60
7	Schottky Barrier Parameters and Low-Frequency Noise Characteristics of Au/Ni Contact to n-Type Î²-Ga2O3. Journal of Electronic Materials, 2020, 49, 297-305.	1.0	12
8	Temperature dependent Schottky barrier characteristics of Al/n-type Si Schottky barrier diode with Auâ€“Cu phthalocyanine interlayer. Thin Solid Films, 2020, 713, 138343.	0.8	10
9	Ar Ion Irradiation Effects on the Characteristics of Ru|Pt|n-GaN Schottky Barrier Diodes. Semiconductors, 2020, 54, 1641-1649.	0.2	0
10	Medium Energy Carbon and Nitrogen Ion Beam Induced Modifications in Charge Transport, Structural and Optical Properties of Ni/Pd/n-GaN Schottky Barrier Diodes. Materials, 2020, 13, 1299.	1.3	1
11	Microstructural and interface properties of Au/SrTiO3 (STO)/n-GaN heterojunction with an e-beam evaporated high-k STO interlayer. Journal of Alloys and Compounds, 2020, 823, 153775.	2.8	9
12	Electrical and carrier transport properties of Au/Pr6O11/n-GaN MIS structure with a high-k rare-earth oxide interlayer at high temperature range. Vacuum, 2020, 174, 109201.	1.6	12
13	Chemical, electrical and carrier transport properties of Au/cytosine/undoped-InP MPS junction with a cytosine polymer. Solid State Sciences, 2019, 97, 105987.	1.5	3
14	Effect of rare-earth Pr6O11 insulating layer on the electrical properties of Au/n-GaN Schottky electrode and its chemical and structural characterization. Journal of Materials Science: Materials in Electronics, 2019, 30, 18710-18719.	1.1	11
15	Microstructural, chemical and electrical characteristics of Au/magnetite (Fe3O4)/n-GaN MIS junction with a magnetite interlayer. Vacuum, 2019, 164, 233-241.	1.6	17
16	Rectifying and breakdown voltage enhancement of Au/n-GaN Schottky diode with Al-doped ZnO films and its structural characterization. Thin Solid Films, 2019, 676, 125-132.	0.8	23
17	Statistical distribution of barrier heights, current conduction mechanism and voltage-dependent capacitanceâ€“frequency characteristics of Au/Fe3O4/n-GaN heterojunction. SN Applied Sciences, 2019, 1, 1.	1.5	1
18	Structural, Chemical and Electrical Properties of Au/La2O3/n-GaN MIS Junction with a High-k Lanthanum Oxide Insulating Layer. Journal of Electronic Materials, 2019, 48, 4217-4225.	1.0	29

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19	Barrier enhancement of Al/n-InP Schottky diodes by graphene oxide thin layer. Indian Journal of Physics, 2019, 93, 467-474.	0.9	5
20	Microstructural, chemical states and electrical properties of Au/CuO/n-InP heterojunction with a cupric oxide interlayer. Vacuum, 2018, 152, 15-24.	1.6	20
21	Effect of copper phthalocyanine thickness on surface morphology, optical and electrical properties of Au/CuPc/n-Si heterojunction. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	1.1	14
22	Effect of annealing on chemical, structural and electrical properties of Au/Gd2O3/n-GaN heterostructure with a high-k rare-earth oxide interlayer. Applied Surface Science, 2018, 427, 670-677.	3.1	68
23	Statistical Analysis of the Currentâ€“Voltage (Iâ€“V) and Capacitanceâ€“Voltage (Câ€“V) Characteristics of the Au/Ir/n-InGaN Schottky Barrier Diodes. Advanced Science Letters, 2018, 24, 5582-5586.	0.2	0
24	Surface chemical states, electrical and carrier transport properties of Au/ZrO2/n-GaN MIS junction with a high-k ZrO2 as an insulating layer. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2018, 231, 74-80.	1.7	25
25	Analysis of Schottky Barrier Parameters and Current Transport Properties of V/p-Type GaN Schottky Junction at Low Temperatures. Journal of Electronic Materials, 2018, 47, 4140-4148.	1.0	4
26	Double Gaussian barrier distribution of permalloy (Ni0.8Fe0.2) Schottky contacts to n-type GaN. Superlattices and Microstructures, 2018, 120, 508-516.	1.4	18
27	Influence of rapid thermal annealing on electrical and structural properties of Pd/Au Schottky contact to Ga-polarity GaN grown on Si (111) substrate. Journal of Alloys and Compounds, 2017, 705, 782-787.	2.8	9
28	Barrier Parameters and Current Transport Characteristics of Ti/p-InP Schottky Junction Modified Using Orange G (OG) Organic Interlayer. Journal of Electronic Materials, 2017, 46, 5746-5754.	1.0	30
29	Surface morphological, electrical and transport properties of rapidly annealed double layers Ru/Cr Schottky structure on n-type InP. Indian Journal of Physics, 2017, 91, 743-753.	0.9	4
30	Electrical and carrier transport properties of the Au/Y2O3/n-GaN metal-insulator-semiconductor (MIS) diode with rare-earth oxide interlayer. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	1.1	19
31	Modification of Schottky barrier properties of Al/p-type Si Schottky rectifiers with graphene-oxide-doped poly(3,4-ethylenedioxythiophene):poly(styrene sulfonate) interlayer. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	5
32	Electrical and frequency-dependent properties of Au/Sm2O3/n-GaN MIS junction with a high-k rare-earth Sm2O3 as interlayer. Current Applied Physics, 2017, 17, 980-988.	1.1	35
33	Microstructural, electrical and frequency-dependent properties of Au/p-Cu2ZnSnS4/n-GaN heterojunction. Journal of Colloid and Interface Science, 2017, 499, 180-188.	5.0	30
34	Effect of seed layers (Al, Ti) on optical and morphology of Fe-doped ZnO thin film nanowires grown on Si substrate via electron beam evaporation. Materials Science in Semiconductor Processing, 2017, 71, 296-303.	1.9	14
35	Schottky barrier parameters and structural properties of rapidly annealed Zr Schottky electrode on p-type GaN. Journal of Semiconductors, 2017, 38, 064001.	2.0	4
36	Electrical and interface properties of PdAl/Au metal alloyed ohmic contacts on p-type GaN for high-temperature MEMS devices. Journal of Materials Science: Materials in Electronics, 2017, 28, 16903-16909.	1.1	8

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37	Electrical transport and current properties of rare-earth dysprosium Schottky electrode on p-type GaN at various annealing temperatures. Journal of Semiconductors, 2017, 38, 114001.	2.0	5
38	Microstructural and electrical properties of Al/n-type Si Schottky diodes with Au-CuPc nanocomposite films as interlayer. Superlattices and Microstructures, 2017, 111, 506-517.	1.4	14
39	Electrical and frequency dependence characteristics of Ti/polyethylene oxide (PEO)/p-type InP organic-inorganic Schottky junction. Journal of Alloys and Compounds, 2017, 695, 2587-2596.	2.8	36
40	Modified electrical properties and transport mechanism of Ti/p-InP Schottky structure with a polyvinylpyrrolidone (PVP) polymer interlayer. Journal of Materials Science: Materials in Electronics, 2017, 28, 4847-4855.	1.1	37
41	Electrical properties and the determination of interface state density from Iâ€“V, Câ€“f and Gâ€“f measurements in Ir/Ru/n-InGaN Schottky barrier diode. Semiconductors, 2017, 51, 1641-1649.	0.2	1
42	Electrical parameters and series resistance analysis of Au/Y/p-InP/Pt Schottky barrier diode at room temperature. AIP Conference Proceedings, 2016, , .	0.3	19
43	Electrical properties and transport mechanisms of Au/Ba0.6Sr0.4TiO3/GaN metalâ€“insulatorâ€“semiconductor (MIS) diode at high temperature range. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	6
44	Effects of Annealing on Electrical Characteristics and Current Transport Mechanisms of the Y/p-GaN Schottky Diode. Journal of Electronic Materials, 2016, 45, 3268-3277.	1.0	4
45	Influence of nanostructure Fe-doped ZnO interlayer on the electrical properties of Au/n-type InP Schottky structure. Materials Chemistry and Physics, 2016, 177, 92-98.	2.0	14
46	Temperature-Dependent Electrical Properties and Carrier Transport Mechanisms of TMAH-Treated Ni/Au/Al2O3/GaN MIS Diode. Journal of Electronic Materials, 2016, 45, 5655-5662.	1.0	14
47	Effect of oxygen plasma treatment on the electrical characteristics of Pt/n-type Si Schottky diodes. Journal of the Korean Physical Society, 2016, 69, 1321-1327.	0.3	1
48	Microstructural, electrical and carrier transport properties of Au/NiO/n-GaN heterojunction with a nickel oxide interlayer. RSC Advances, 2016, 6, 105761-105770.	1.7	58
49	Effects of high-k zirconium oxide (ZrO2) interlayer on the electrical and transport properties of Au/n-type InP Schottky diode. Thin Solid Films, 2016, 619, 231-238.	0.8	27
50	Modification of electrical properties of Au/n-type InP Schottky diode with a high-k Ba 0.6 Sr 0.4 TiO 3 interlayer. Superlattices and Microstructures, 2016, 93, 82-91.	1.4	31
51	Effect of annealing temperature on the electrical and structural properties of V/p-GaN Schottky structures. Thin Solid Films, 2016, 598, 236-242.	0.8	17
52	Transport mechanisms and interface properties of W/p-InP Schottky diode at room temperature. Indian Journal of Physics, 2016, 90, 399-406.	0.9	7
53	Modification of Schottky Barrier Properties of Ti/p-type InP Schottky Diode by Polyaniline (PANI) Organic Interlayer. Journal of Semiconductor Technology and Science, 2016, 16, 664-674.	0.1	25
54	Ru/Ti Schottky Contacts on N-type In-P (100): Temperature Dependence of Current-Voltage (I-V) Characteristics. , 2015, 10, 666-672.		5

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55	Temperature Dependent Current-Voltage and Capacitance-Voltage Characteristics of an Au/n-Type Si Schottky Barrier Diode Modified Using a PEDOT:PSS Interlayer. Materials Transactions, 2015, 56, 10-16.	0.4	22
56	Determination of the characteristic parameters of Au/PVDF/n-InP Schottky structure from current-voltage and capacitance-voltage measurements. AIP Conference Proceedings, 2015, , .	0.3	3
57	Annealing effects on the electrical, structural and morphological properties of Ti/p-GaN/Ni/Au Schottky diode. Applied Physics A: Materials Science and Processing, 2015, 121, 131-140.	1.1	13
58	Electrical parameters and current conduction mechanism in Cr/Au/n-InP Schottky structure at different annealing temperatures. AIP Conference Proceedings, 2015, , .	0.3	1
59	Temperature-dependent electrical parameters and current transport mechanisms of Ru/Ti/n-InP Schottky diodes. Indian Journal of Physics, 2015, 89, 1161-1168.	0.9	7
60	Rapid thermal annealing effects on the electrical, structural and morphological properties of Yb/p-type InP Schottky Structure. Electronic Materials Letters, 2015, 11, 73-81.	1.0	12
61	Electrical properties and carrier transport mechanism in V/p-GaN Schottky diode at high temperature range. Superlattices and Microstructures, 2015, 86, 157-165.	1.4	9
62	Effect of annealing temperature on the electrical, structural and surface morphological properties of Ru/Ti Schottky contacts on n -type InP. Superlattices and Microstructures, 2015, 86, 280-291.	1.4	7
63	Effect of thermal annealing on the electrical and structural properties of Au/Y/p-type InP Schottky structure. Vacuum, 2015, 119, 276-283.	1.6	10
64	Electrical and interfacial properties of Au/n-InP Schottky contacts with nickel phthalocyanine (NiPc) interlayer. Indian Journal of Physics, 2015, 89, 463-469.	0.9	21
65	Energy-level alignment and electrical properties of Al/p-type Si Schottky diodes with sorbitol-doped PEDOT:PSS as an organic interlayer. Journal of Alloys and Compounds, 2015, 637, 84-89.	2.8	22
66	Rapid thermal annealing effects on the electrical and structural properties of Ru/V/n-InP Schottky barrier diode. Superlattices and Microstructures, 2015, 83, 48-60.	1.4	5
67	Double Gaussian Distribution of Barrier Heights, Interface States, and Current Transport Mechanisms in Au/Bi0.5Na0.5TiO3-BaTiO3/n-GaN MIS Structure. Journal of Electronic Materials, 2015, 44, 549-557.	1.0	21
68	Effect of copper phthalocyanine (CuPc) interlayer on the electrical characteristics of Au/n-GaN Schottky rectifier. Materials Science in Semiconductor Processing, 2015, 30, 420-428.	1.9	10
69	Electrical properties of Au/Bi0.5Na0.5TiO3-BaTiO3/n-GaN metalâ€“insulatorâ€“semiconductor (MIS) structure. Semiconductor Science and Technology, 2014, 29, 075001.	1.0	18
70	Effect of annealing on the electrical and interface properties of Au/PVC/n-InP organic-on-inorganic structures. Microelectronic Engineering, 2014, 114, 31-37.	1.1	11
71	Electrical properties and conduction mechanism of an organic-modified Au/NiPc/n-InP Schottky barrier diode. Applied Physics A: Materials Science and Processing, 2014, 116, 1379-1387.	1.1	24
72	CdS microflowers and interpenetrated nanorods grown on Si substrate: Structural, optical properties and growth mechanism. Materials Chemistry and Physics, 2014, 146, 399-405.	2.0	5

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73	Electrical properties and the role of inhomogeneities at the polyvinyl alcohol/nâ€inp schottky barrier interface. Journal of Applied Polymer Science, 2014, 131, .	1.3	19
74	Electrical and structural properties of rapidly annealed rare-earth metal Er Schottky contacts on p-type InP. Superlattices and Microstructures, 2014, 65, 206-218.	1.4	13
75	Influence of annealing temperature on the electrical and structural properties of palladium Schottky contacts on n-type 4Hâ€“SiC. Superlattices and Microstructures, 2014, 76, 55-65.	1.4	10
76	Modified electrical characteristics of Pt/n-type Ge Schottky diode with a pyronine-B interlayer. Superlattices and Microstructures, 2014, 75, 806-817.	1.4	22
77	Influence of annealing effects on the electrical and microstructural properties of Se Schottky contacts on n-type GaN. Journal of Materials Science: Materials in Electronics, 2014, 25, 2379-2386.	1.1	4
78	Electrical Properties and Current Transport Mechanisms of the Au/n-GaN Schottky Structure with Solution- Processed High-k BaTiO3 Interlayer. Journal of Electronic Materials, 2014, 43, 3499-3507.	1.0	80
79	Influence of tetramethylammonium hydroxide treatment on the electrical characteristics of Ni/Au/GaN Schottky barrier diode. Materials Chemistry and Physics, 2014, 143, 801-805.	2.0	11
80	Electronic parameters and carrier transport mechanism of high-barrier Se Schottky contacts to n-type GaN. Solid State Communications, 2014, 179, 34-38.	0.9	12
81	Electrical and structural properties of tungsten Schottky contacts to p-type InP at different annealing temperatures. Superlattices and Microstructures, 2014, 71, 134-146.	1.4	7
82	XPS study of sputtered alumina thin films. Ceramics International, 2014, 40, 11099-11107.	2.3	68
83	Pulsed rf magnetron sputtered alumina thin films. Ceramics International, 2014, 40, 9571-9582.	2.3	32
84	Electrical properties and the double Gaussian distribution of inhomogeneous barrier heights in Se/n-GaN Schottky barrier diode. Superlattices and Microstructures, 2014, 67, 242-255.	1.4	32
85	Electrical properties of Au/polyvinylidene fluoride/n-InP Schottky diode with polymer interlayer. Thin Solid Films, 2014, 556, 300-306.	0.8	119
86	High emittance surface engineered metallic surfaces. Ceramics International, 2014, 40, 14549-14554.	2.3	4
87	Electrical Properties and Carrier Transport Mechanism of Au/<i>n</i>-GaN Schottky Contact Modified Using a Copper Pthalocyanine (CuPc) Interlayer. Materials Transactions, 2014, 55, 758-762.	0.4	13
88	Electrical properties of Ir/n-InGaN/Ti/Al Schottky barrier diode in a wide temperature range. Advanced Materials Letters, 2014, 5, 31-38.	0.3	15
89	Temperature-Dependent Currentâ€“Voltage (Iâ€“V) and Capacitanceâ€“Voltage (Câ€“V) Characteristics of Ni/Cu/n-InP Schottky Barrier Diodes. Brazilian Journal of Physics, 2013, 43, 13-21.	0.7	18
90	Influence of Annealing on Electrical Properties of an Organic Thin Layer-Based n-Type InP Schottky Barrier Diode. Journal of Electronic Materials, 2013, 42, 1282-1289.	1.0	12

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91	Development of SiO2 based thin film on metal foils for space application. Ceramics International, 2013, 39, 8493-8498.	2.3	15
92	Optical and Microstructural Characterisations of Pulsed rf Magnetron Sputtered Alumina Thin Film. Journal of Materials Science and Technology, 2013, 29, 929-936.	5.6	20
93	Electrical properties of Au/n-InP and Au/PVA/n-InP Schottky structures. , 2013, , .		0
94	Electrical properties of Pt/n-type Ge Schottky contact with PEDOT:PSS interlayer. Journal of Alloys and Compounds, 2013, 549, 18-21.	2.8	40
95	Capacitanceâ€“frequency (Câ€“f) and conductanceâ€“frequency (Gâ€“f) characteristics of Ir/n-InGaN Schottky diode as a function of temperature. Superlattices and Microstructures, 2013, 60, 358-369.	1.4	40
96	Depinning of the Fermi level at the Ge Schottky interface through Se treatment. Scripta Materialia, 2013, 69, 809-811.	2.6	9
97	Effect of annealing on the electronic parameters of Au/poly(ethylmethacrylate)/n-InP Schottky diode with organic interlayer. Current Applied Physics, 2013, 13, 1604-1610.	1.1	38
98	Analysis of electrical properties and deep level defects in undoped GaN Schottky barrier diode. Thin Solid Films, 2013, 534, 603-608.	0.8	25
99	Analysis of electrical characteristics of Er/p-InP Schottky diode at high temperature range. Current Applied Physics, 2013, 13, 975-980.	1.1	27
100	Electrical and structural properties of Ir/Ru Schottky rectifiers on n-type InGaN at different annealing temperatures. Superlattices and Microstructures, 2013, 56, 64-76.	1.4	26
101	Effect of annealing temperature on the electrical properties of Au/Ta2O5/n-GaN metalâ€“insulatorâ€“semiconductor (MIS) structure. Applied Physics A: Materials Science and Processing, 2013, 113, 713-722.	1.1	15
102	Thermal annealing effects on electrical properties of Ir/Ru Schottky contacts on n-InGaN. , 2013, , .		0
103	Temperature dependent electrical properties of rare-earth metal Er Schottky contact on p-type InP. , 2013, , .		0
104	Electrical Properties and Interface States of Rare-Earth Metal Ytterbium Schottky Contacts to p-Type InP. Materials Transactions, 2013, 54, 2173-2179.	0.4	17
105	Effect of Rapid Thermal Annealing on the Electrical and Structural Properties of Se Schottky Contacts to n-Type Si. Materials Transactions, 2013, 54, 1067-1072.	0.4	5
106	Influence of Series Resistance and Interface State Density on Electrical Characteristics of Ru/Ni/n-GaN Schottky structure. Journal of Semiconductor Technology and Science, 2013, 13, 492-499.	0.1	9
107	Temperature Dependency And Current Transport Mechanisms Of Pd/V/n-type InP Schottky Rectifiers. Advanced Materials Letters, 2012, 3, 188-196.	0.3	39
108	Analysis of temperature-dependent Schottky barrier parameters of Cuâ€“Au Schottky contacts to n-InP. Canadian Journal of Physics, 2012, 90, 73-81.	0.4	7

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109	SYNTHESIS AND CHARACTERIZATION OF NICKEL DOPED CdS NANOPARTICLES. International Journal of Nanoscience, 2012, 11, 1240006.	0.4	9
110	Effect of temperature on series resistance determination of Au/polyvinyl alcohol/n-InP Schottky structures. , 2012, , .		0
111	Current transport mechanisms in Ru/Pd/n-GaN Schottky barrier diodes and deep level defect studies. Superlattices and Microstructures, 2012, 52, 484-499.	1.4	11
112	Electrical Properties of Rapidly Annealed Ir and Ir/Au Schottky Contacts on n-Type InGaN. Journal of Metallurgy, 2012, 2012, 1-9.	1.1	10
113	Electrical and structural properties of Pd/V/nâ€type InP (111) Schottky structure as a function of annealing temperature. Surface and Interface Analysis, 2012, 44, 98-104.	0.8	5
114	Influence of annealing on structural and electrical properties of double metal structure Ru/Cu contacts on nâ€type InP. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 105-112.	0.8	3
115	Annealing effects on electrical, structural, and surface morphological properties of Ir/n-InGaN Schottky structures. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2027-2033.	0.8	4
116	Barrier characteristics of Pt/Ru Schottky contacts on n-type GaN based on Iâ€“Vâ€“T and Câ€“Vâ€“T measurements. Bulletin of Materials Science, 2012, 35, 53-61.	0.8	25
117	Electrical transport properties of Ru/Cu/n-InP Schottky barrier diode based on temperature-dependent Iâ€“V and Câ€“V measurements. Indian Journal of Physics, 2012, 86, 687-695.	0.9	7
118	Electrical transport properties of Au/SiO2/n-GaN MIS structure in a wide temperature range. Current Applied Physics, 2012, 12, 765-772.	1.1	43
119	Effect of annealing temperature on electrical properties of Au/polyvinyl alcohol/n-InP Schottky barrier structure. Thin Solid Films, 2012, 520, 5715-5721.	0.8	34
120	Annealing Effects on Electrical Properties and Interfacial Reactions of Ni/Cu Schottky Rectifiers on n-Type InP. Journal of Modern Physics, 2012, 03, 538-545.	0.3	11
121	Electrical characterization of Au/n-GaN metalâ€“semiconductor and Au/SiO2/n-GaN metalâ€“insulatorâ€“semiconductor structures. Journal of Alloys and Compounds, 2011, 509, 8001-8007.	2.8	75
122	Temperature-dependent Schottky barrier characteristics of Cuâ•Au Schottky contacts to n-InP. , 2011, , .		0
123	Influence of rapid thermal annealing effect on electrical and structural properties of Pd/Ru Schottky contacts to n-type GaN. Materials Chemistry and Physics, 2011, 130, 1000-1006.	2.0	15
124	Electrical and structural properties of double metal structure Ni/V Schottky contacts on n-InP after rapid thermal process. Journal of Materials Science, 2011, 46, 558-565.	1.7	9
125	Microstructural and electrical characteristics of rapidly annealed Ni/Mo Schottky rectifiers on cleaned n-type GaN (0001) surface. Journal of Materials Science: Materials in Electronics, 2011, 22, 286-291.	1.1	5
126	Electrical, structural and morphological characteristics of rapidly annealed Pd/n-InP (100) Schottky structure. Journal of Materials Science: Materials in Electronics, 2011, 22, 854-861.	1.1	5

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127	Electrical characteristics and interfacial reactions of rapidly annealed Pt/Ru Schottky contacts on nâ€type GaN. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1670-1677.	0.8	8
128	Structural, electrical, and surface morphological characteristics of rapidly annealed Pt/Ti Schottky contacts to nâ€type InP. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 2406-2414.	0.8	6
129	Electrical, structural and morphological characteristics of rapidly annealed Ni/Pd Schottky rectifiers on nâ€type GaN. Surface and Interface Analysis, 2011, 43, 1251-1256.	0.8	4
130	Study of deep level defect behavior in undoped n-InP (100) after rapid thermal annealing. Microelectronic Engineering, 2011, 88, 506-508.	1.1	1
131	Electrical transport characteristics of Ni/Pd/n-GaN Schottky barrier diodes as a function of temperature. Thin Solid Films, 2011, 519, 3844-3850.	0.8	41
132	Electrical Properties of Pt/n-Ge Schottky Contact Modified Using Copper Phthalocyanine (CuPc) Interlayer. Journal of the Electrochemical Society, 2011, 159, H33-H37.	1.3	31
133	Double Gaussian Distribution of Inhomogeneous Barrier Height in Ruâ•Ptâ•n-GaN Schottky Barrier Diodes. , 2011, , .		0
134	Analysis of currentâ€“voltageâ€“temperature (â€“â€“) and capacitanceâ€“voltageâ€“temperature (â€“â€“) characteristics of Ni/Au Schottky contacts on n-type InP. Superlattices and Microstructures, 2010, 48, 330-342.	1.4	36
135	Investigation on deep level defects in rapid thermal annealed undoped n-type InP. Journal of Materials Science: Materials in Electronics, 2010, 21, 285-290.	1.1	4
136	The influence of rapid thermal annealing on electrical and structural properties of Pt/Au Schottky contacts to n-type InP. Journal of Materials Science: Materials in Electronics, 2010, 21, 804-810.	1.1	6
137	Electrical, structural and surface morphological properties of thermally stable low-resistance W/Ti/Au multilayer ohmic contacts to n-type GaN. Applied Surface Science, 2010, 257, 67-71.	3.1	3
138	Effect of rapid thermal annealing on deep level defects in the Si-doped GaN. Microelectronic Engineering, 2010, 87, 117-121.	1.1	13
139	Influence of rapid thermal annealing on electrical and structural properties of double metal structure Au/Ni/n-InP (111) diodes. Current Applied Physics, 2010, 10, 687-692.	1.1	12
140	Structural and electrical properties of rapidly annealed Ni/Mo Schottky barriers on nâ€type GaN. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 753-759.	0.8	8
141	Electrical properties and interfacial reactions of rapidly annealed Ni/Ru Schottky rectifiers on n-type GaN. Journal of Alloys and Compounds, 2010, 503, 186-191.	2.8	20
142	Analysis of the currentâ€“voltage characteristics of the Pd/Au Schottky structure on n-type GaN in a wide temperature range. Semiconductor Science and Technology, 2009, 24, 035004.	1.0	52
143	Effect of annealing temperature on electrical and structural properties of transparent indium tin oxide electrode to n-type GaN. Materials Chemistry and Physics, 2009, 114, 821-826.	2.0	16
144	Evaluation of Schottky barrier parameters of Pd/Pt Schottky contacts on n-InP (100) in wide temperature range. Superlattices and Microstructures, 2009, 45, 22-32.	1.4	16

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145	Thermally stable and low-resistance W/Ti/Au contacts to n-type GaN. Journal of Materials Science: Materials in Electronics, 2009, 20, 9-13.	1.1	3
146	Effects of thermal annealing on the electrical and structural properties of Pt/Mo Schottky contacts on n-type GaN. Journal of Materials Science: Materials in Electronics, 2009, 20, 1018-1025.	1.1	19
147	Rapid thermal annealing effects on electrical and structural properties of Pd/Au Schottky contacts to nâ€type InP(111). Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 250-255.	0.8	10
148	Effect of rapid thermal annealing on the electrical and structural properties of Ru/nâ€InP (100) Schottky rectifiers. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2658-2664.	0.8	8
149	Effects of annealing temperature on electrical and structural properties of Mo/nâ€InP (100) Schottky contacts. Surface and Interface Analysis, 2009, 41, 905-910.	0.8	8
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